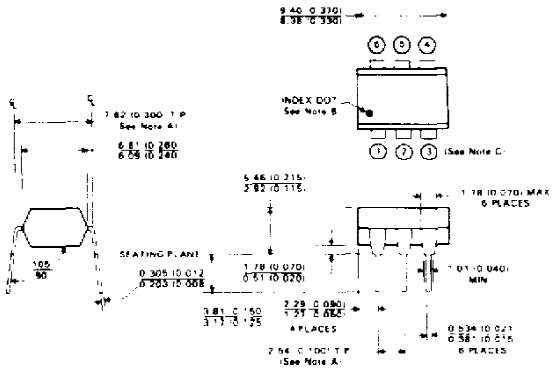
SOOS040 D1607, NOVEMBER 1973–REVISED FEBRUARY 1983

COMPATIBLE WITH STANDARD TTL INTEGRATED CIRCUITS

- **Gallium Arsenide Diode Infrared Source Optically Coupled to a Silicon N-P-N Phototransistor**
- **High Direct-Current Transfer Ratio**
- **High-Voltage Electrical Isolation . . . 1.5-kV or 2.5-kV Rating**
- **Plastic Dual-In-Line Package**
- **High-Speed Switching: t_r = 5 μs, t_f = 5 μs Typical**

mechanical data

The package consists of a gallium arsenide infrared-emitting diode and an n-p-n silicon phototransistor mounted on a 6-lead frame encapsulated within an electrically nonconductive plastic compound. The case will withstand soldering temperature with no deformation and device performance characteristics remain stable when operated in high-humidity conditions. Unit weight is approximately 0.52 grams.



NOTES:
a. Leads are within 0.13 mm (0.005 inch) radius of true position (T.P.) with maximum material condition and unit installed.
b. Pin 1 identified by index dot.
c. Terminal connections:
1. Anode } Infrared-emitting diode
2. Cathode
3. No internal connection
4. Emitter } Phototransistor
5. Collector
6. Base

FALLS WITHIN JEDEC MO-001AM DIMENSIONS
ALL LINEAR DIMENSIONS ARE IN MILLIMETERS AND PARENTHETICALLY IN INCHES

absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Input-to-Output Voltage: TIL111	±1.5 kV
TIL114, TIL116, TIL117	±2.5 kV
Collector-Base Voltage	70 V
Collector-Emitter Voltage (See Note 1)	30 V
Emitter-Collector Voltage	7 V
Emitter-Base Voltage	7 V
Input-Diode Reverse Voltage	3 V
Input Diode Continuous Forward Current at (or below) 25°C Free-Air Temperature (See Note 2)	100 mA
Continuous Power Dissipation at (or below) 25°C Free-Air Temperature:	
Infrared-Emitting Diode (See Note 3)	150 mW
Phototransistor (See Note 4)	150 mW
Total, Infrared-Emitting Diode plus Phototransistor (See Note 5)	250 mW
Storage Temperature Range	−55°C to 150°C
Lead Temperature 1,6 mm (1/16 Inch) from Case for 10 Seconds	260°C

NOTES: 1. This value applies when the base-emitter diode is open-circuited.
2. Derate linearly to 100°C free-air temperature at the rate of 1.33 mA/°C.
3. Derate linearly to 100°C free-air temperature at the rate of 2 mW/°C.
4. Derate linearly to 100°C free-air temperature at the rate of 2 mW/°C.
5. Derate linearly to 100°C free-air temperature at the rate of 3.33 mW/°C.

electrical characteristics at 25°C free-air temperature

PARAMETER			TEST CONDITIONS	TIL111 TIL114			TIL116			TIL117			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage		I_C = 10 μA, I_E = 0, I_F = 0	70			70			70			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage		I_C = 1 mA, I_B = 0, I_F = 0	30			30			30			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage		I_E = 10 μA, I_C = 0, I_F = 0	7			7			7			V
I_R	Input Diode Static Reverse Current		V_R = 3 V			10			10			10	μA
$I_{C(on)}$	On-State Collector Current	Phototransistor Operation	V_{CE} = 0.4 V, I_F = 16 mA, I_B = 0	2	7								mA
			V_{CE} = 10 V, I_F = 10 mA, I_B = 0				2	5		5	9		
		Photodiode Operation	V_{CB} = 0.4 V, I_F = 16 mA, I_E = 0	7	20		7	20		7	20		μA
$I_{C(off)}$	Off-State Collector Current	Phototransistor Operation	V_{CE} = 10 V, I_F = 0, I_B = 0		1	50		1	50		1	50	nA
		Photodiode Operation	V_{CB} = 10 V, I_F = 0, I_E = 0		0.1	20		0.1	20		0.1	20	
h_{FE}	Transistor Static Forward Current Transfer Ratio		V_{CE} = 5 V, I_C = 10 mA, I_F = 0	100	300					200	550		
			V_{CE} = 5 V, I_C = 100 μA, I_F = 0				100	300					
V_F	Input Diode Static Forward Voltage		I_F = 16 mA		1.2	1.4					1.2	1.4	V
			I_F = 60 mA					1.25	1.5				
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		I_C = 2 mA, I_F = 16 mA, I_B = 0		0.25	0.4							V
			I_C = 2.2 mA, I_F = 15 mA, I_B = 0					0.25	0.4				
			I_C = 0.5 mA, I_F = 10 mA, I_B = 0								0.25	0.4	
r_{IO}	Input-to-Output Internal Resistance		V_{in-out} = ±1.5 kV for TIL111, ±2.5 kV for all others, See Note 6	10^{11}			10^{11}			10^{11}			Ω
C_{io}	Input-to-Output Capacitance		V_{in-out} = 0, f = 1 MHz, See Note 6		1	1.3		1	1.3		1	1.3	pF

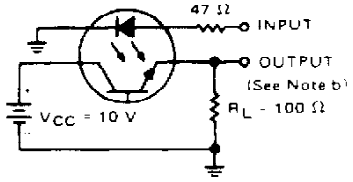
NOTE 6: These parameters are measured between both input diode leads shorted together and all the phototransistor leads shorted together.

switching characteristics at 25°C free-air temperature

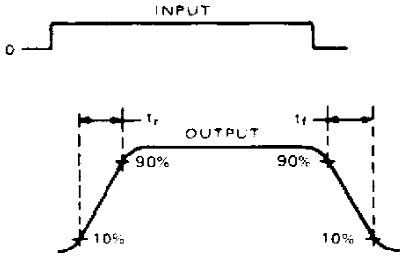
PARAMETER			TEST CONDITIONS	TIL111 TIL114			TIL116			TIL117			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_r	Rise Time	Phototransistor Operation	V_{CC} = 10 V, $I_{C(on)}$ = 2 mA, R_L = 100 Ω, See Test Circuit A of Figure 1		5	10		5	10		5	10	μs
t_f	Fall Time				5	10		5	10		5	10	
t_r	Rise Time	Photodiode Operation	V_{CC} = 10 V, $I_{C(on)}$ = 20 μA, R_L = 1 kΩ, See Test Circuit B of Figure 1		1			1			1		μs
t_f	Fall Time				1			1			1		

PARAMETER MEASUREMENT INFORMATION

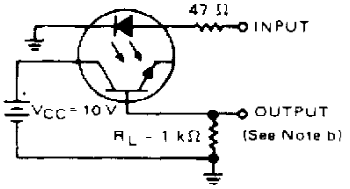
Adjust amplitude of input pulse for:
$I_{C(on)}$ = 2 mA (Test Circuit A) or
$I_{C(on)}$ = 20 μA (Test Circuit B)



TEST CIRCUIT A
PHOTOTRANSISTOR OPERATION



VOLTAGE WAVEFORMS



TEST CIRCUIT B
PHOTODIODE OPERATION

NOTES a. The input waveform is supplied by a generator with the following characteristics: Z_{out} = 50 Ω, t_r = 15 ns, duty cycle = 1%, t_w = 100 μs.
b. The output waveform is monitored on an oscilloscope with the following characteristics: t_r = 12 ns, R_{in} = 1 MΩ, C_{in} = 20 pF.

FIGURE 1–SWITCHING TIMES

TYPICAL CHARACTERISTICS

TIL111, TIL114

COLLECTOR CURRENT
vs
INPUT-DIODE FORWARD CURRENT

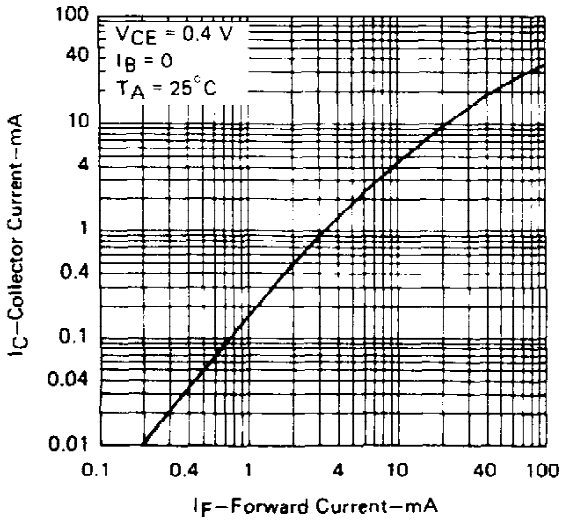


FIGURE 2

TIL116, TIL117

COLLECTOR CURRENT
vs
INPUT-DIODE FORWARD CURRENT

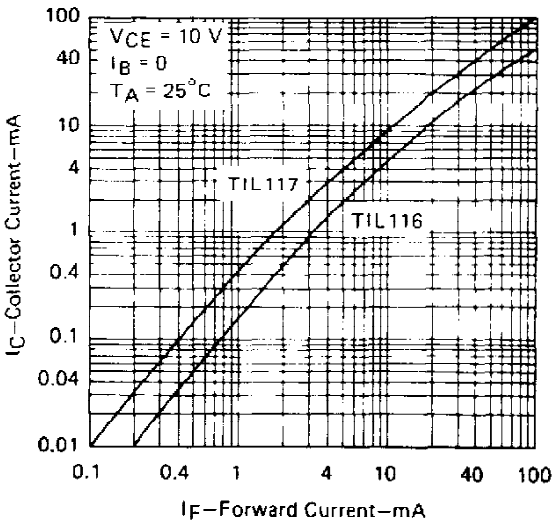


FIGURE 3

TYPICAL CHARACTERISTICS

TIL111, TIL114

COLLECTOR CURRENT
vs
COLLECTOR-EMITTER VOLTAGE

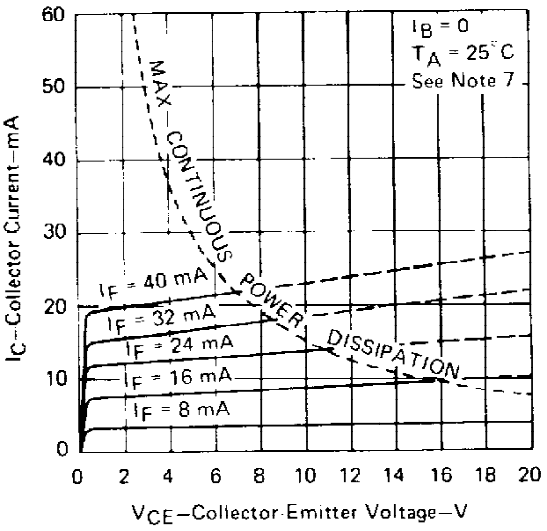


FIGURE 4

TIL116

COLLECTOR CURRENT
vs
COLLECTOR-EMITTER VOLTAGE

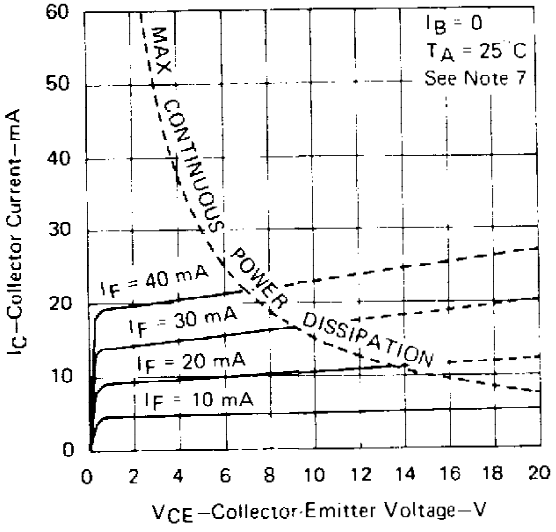


FIGURE 5

TIL117

COLLECTOR CURRENT
vs
COLLECTOR-EMITTER VOLTAGE

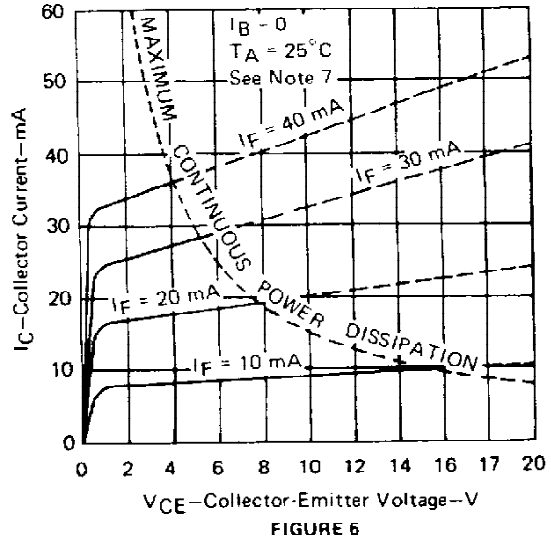


FIGURE 6

RELATIVE ON-STATE COLLECTOR CURRENT
vs
FREE-AIR TEMPERATURE

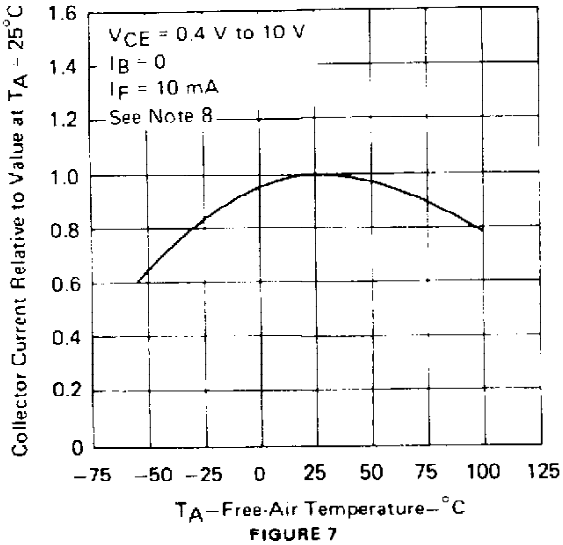


FIGURE 7

NOTES: 7. Pulse operation of input diode is required for operation beyond limits shown by dotted lines.
8. These parameters were measured using pulse techniques. t_w = 1 ms, duty cycle ≤ 2%.

TYPICAL CHARACTERISTICS

OFF-STATE COLLECTOR CURRENT
vs
FREE-AIR TEMPERATURE

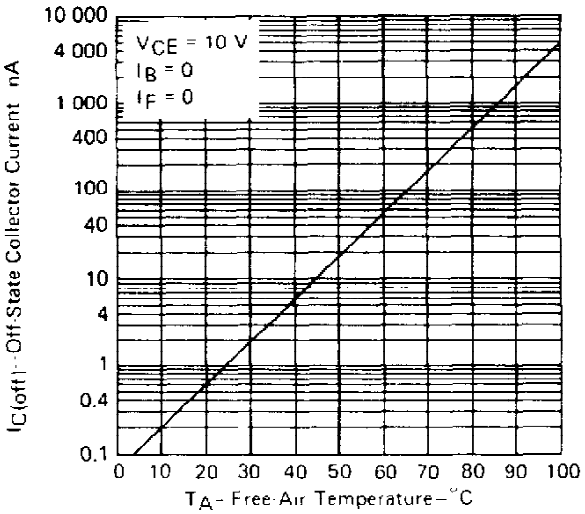


FIGURE 8

NORMALIZED TRANSISTOR STATIC FORWARD
CURRENT TRANSFER RATIO
vs
ON-STATE COLLECTOR CURRENT

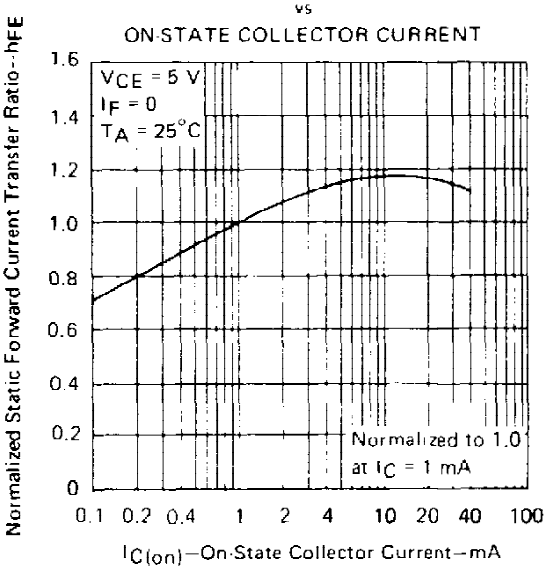


FIGURE 9

INPUT DIODE FORWARD
CONDUCTION CHARACTERISTICS

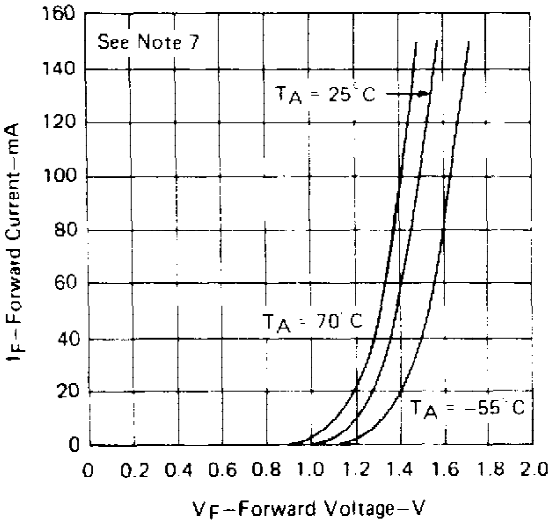


FIGURE 10

COLLECTOR CURRENT
vs
MODULATION FREQUENCY

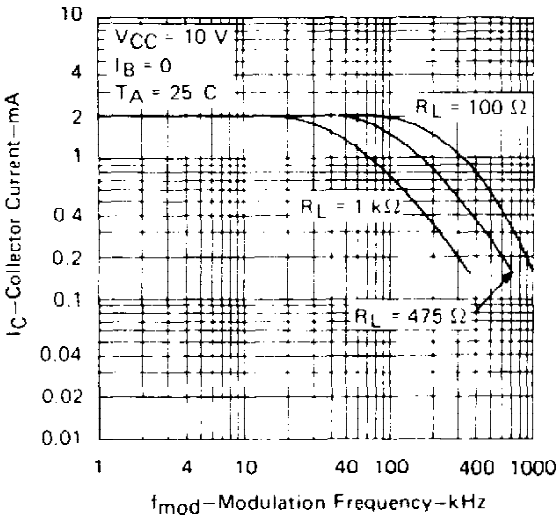


FIGURE 11

NOTE 7: These parameters were measured using pulse techniques, t_w = 1 ms, duty cycle ≤ 2%.

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